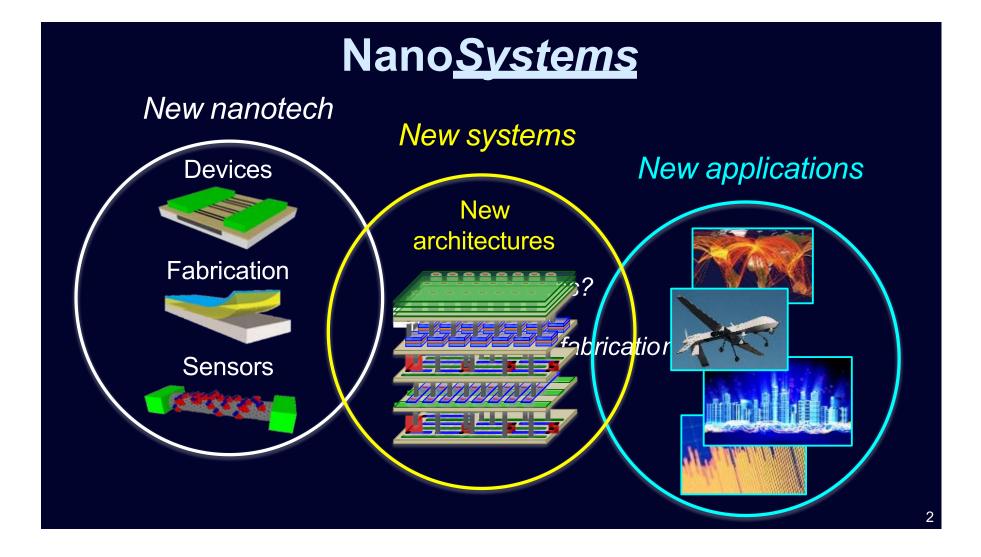
NanoSystems The N3XT 1,000×

Subhasish Mitra

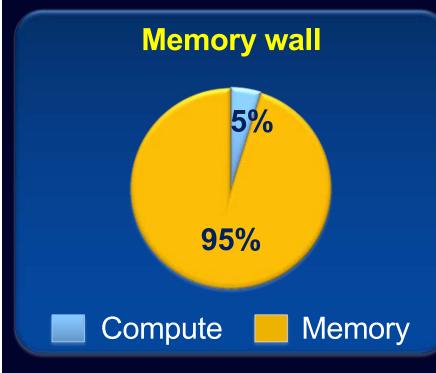


Department of EE & Department of CS Stanford University



Application Challenges

Abundant-data apps.



Brain-inspired \supset Neural Nets

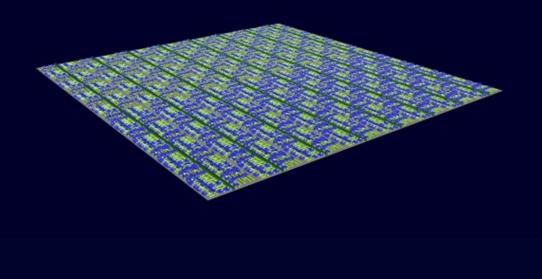
Chip realization ?

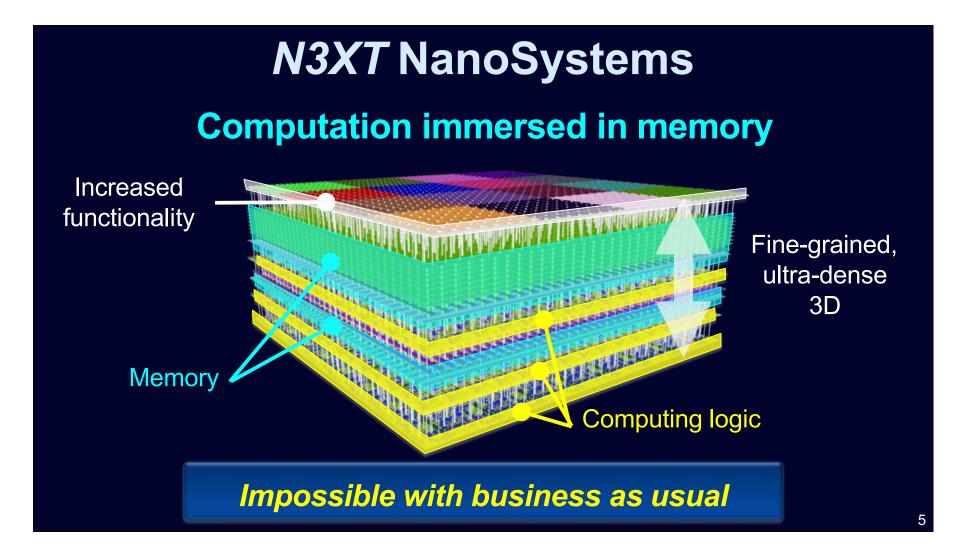
- Compute + memory
- Dense connectivity
- Energy efficiency

• Footprint

N3XT NanoSystems

Computation immersed in memory





Nano-Engineered Computing Systems Technology





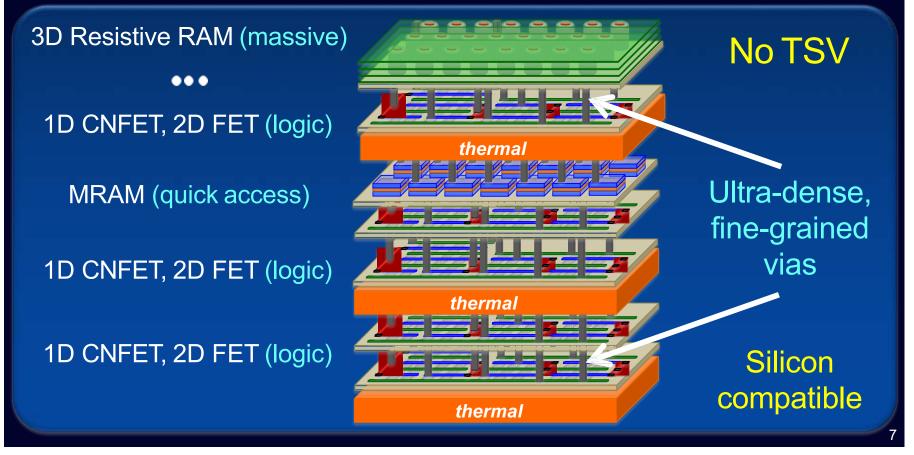
INVITED

The N3XT Approach to Energy-Efficient Abundant-Data Computing

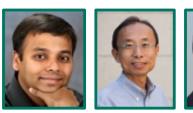
This paper enables energy-efficient computing for transformative abundant-data applications through heterogeneous integration of energy-efficient logic devices immersed in dense nonvolatile memory, with fine-grained connectivity in a monolithic 3-D architecture.

[Aly IEEE Computer 15, Proc. IEEE 19] Stanford + CMU + MIT + NTU Singapore + UC Berkeley + U. Michigan

N3XT Computation Immersed in Memory



DARPA 3DSoC Program



Subhasish Mitra H.-S. Philip Wong, Simon S. Wong

Nan^{*}Integris



Max Shulaker Anantha Chandrakasan

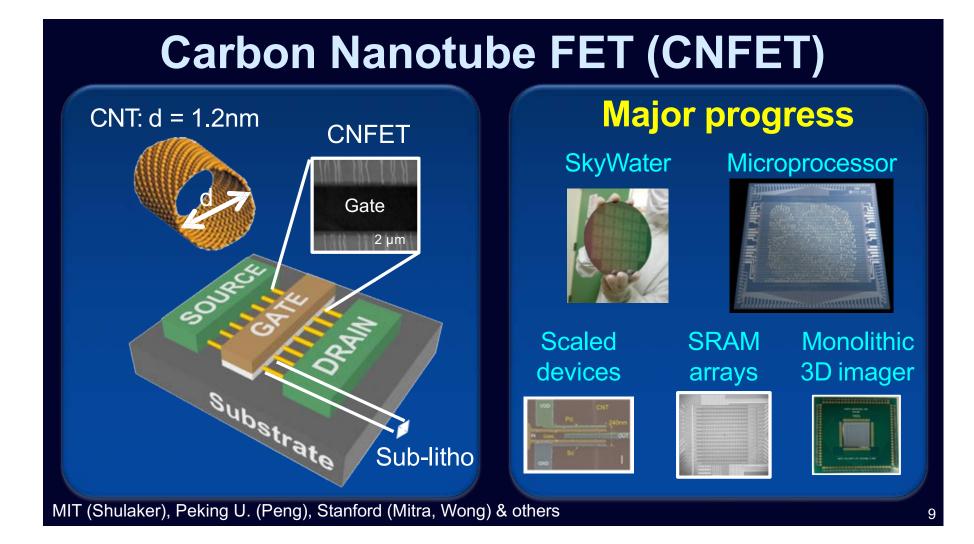


Brad Ferguson Mark Nelson



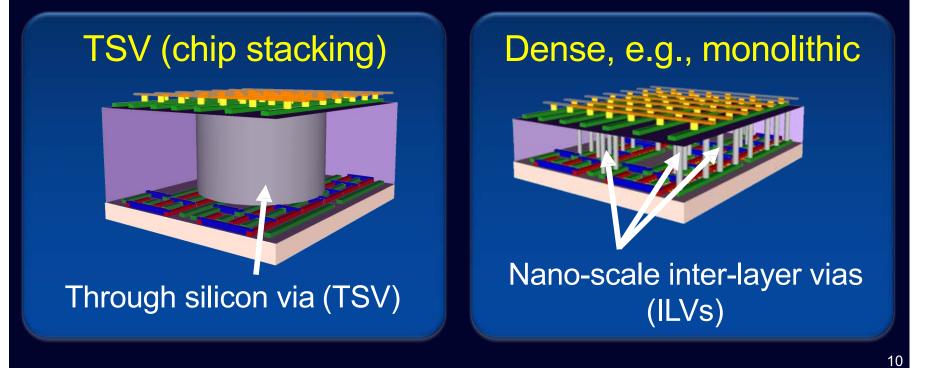
Jefford Humes

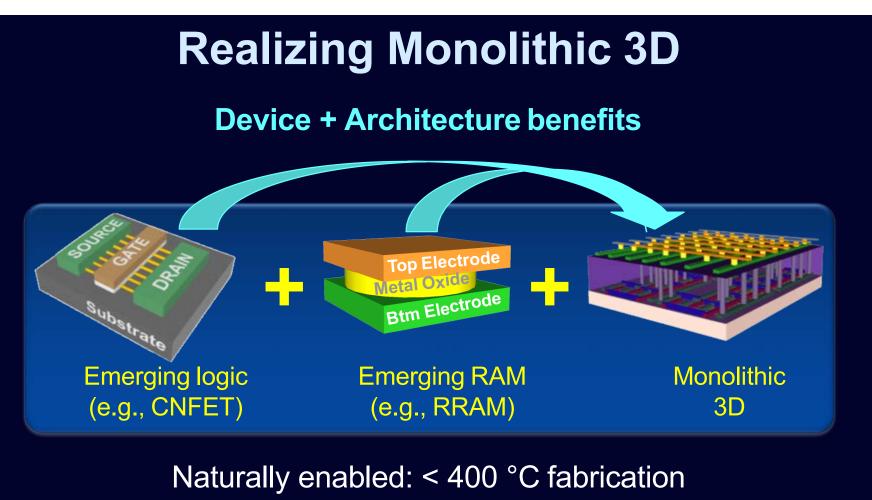




3D Integration

Massive ILV density >> TSV density





Foundry CNFET + RRAM + Monolithic 3D

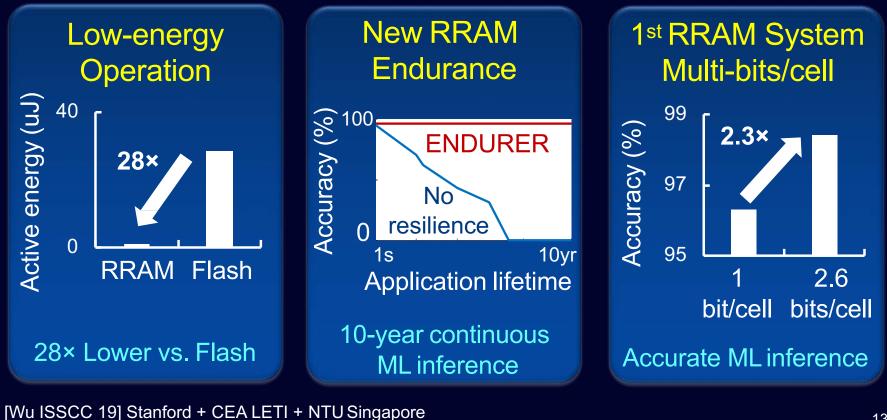
First 3D Nanotube and RRAM ICs Come Out of Foundry

SkyWater Technology Foundry produces first wafers in a drive to match performance of cutting-edge silicon chips

By Samuel K. Moore



RRAM Advances

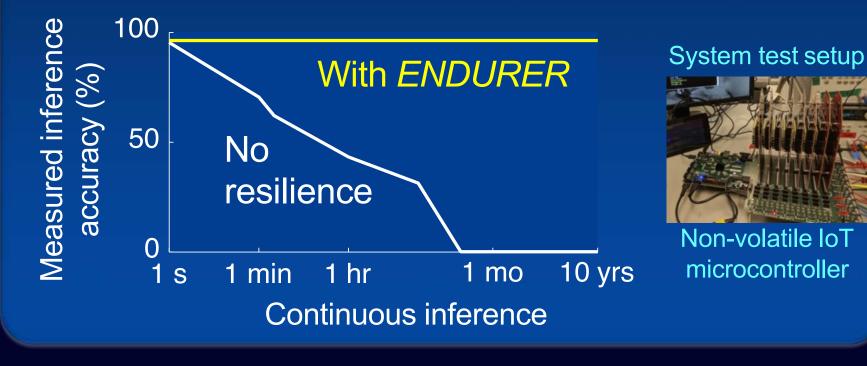


First Multiple bits-per-cell RRAM System

	Bits per cell	Cells measured	Neural nets Optimized weight encoding
Our work new algorithms	3	Full arrays	T Cross-layer RRAM arrays multiple bits-per-cell
Prior work ad hoc	2-6.5	Single cell, few hand-picked cells	2.3× accurate inference Same hardware, bigger model

ENDURER

10-year lifetime (measured)



N3XT Cross-Layer ModSim

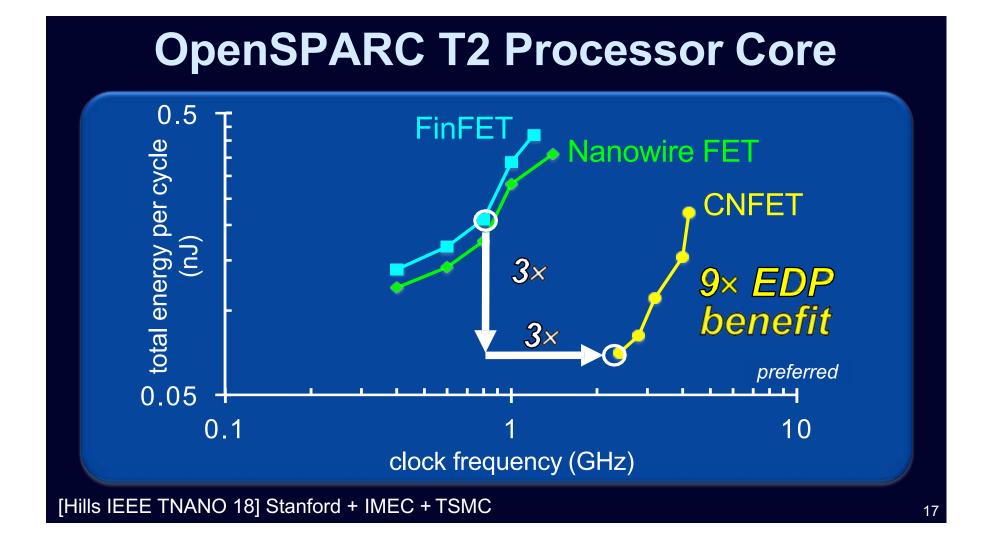
Many chips system

Few chips system

Architecture

Circuit

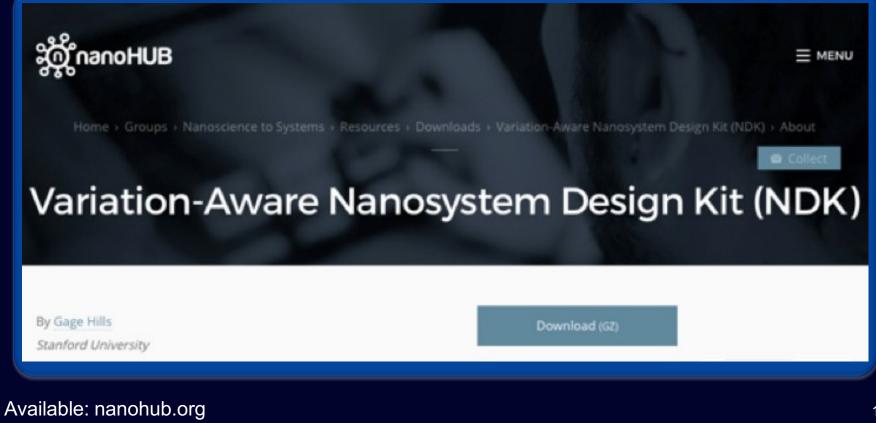
Device



Many FAQs Answered

- 1. Where do benefits come from ?
- 2. Wires limit performance ? Why research FETs ?
- **3**. CNFET contact resistance ?
- 4. Aren't FETs good enough already ?
- **5**. CNT variations ?

NanoSystem Design Kit



N3XT Cross-Layer ModSim

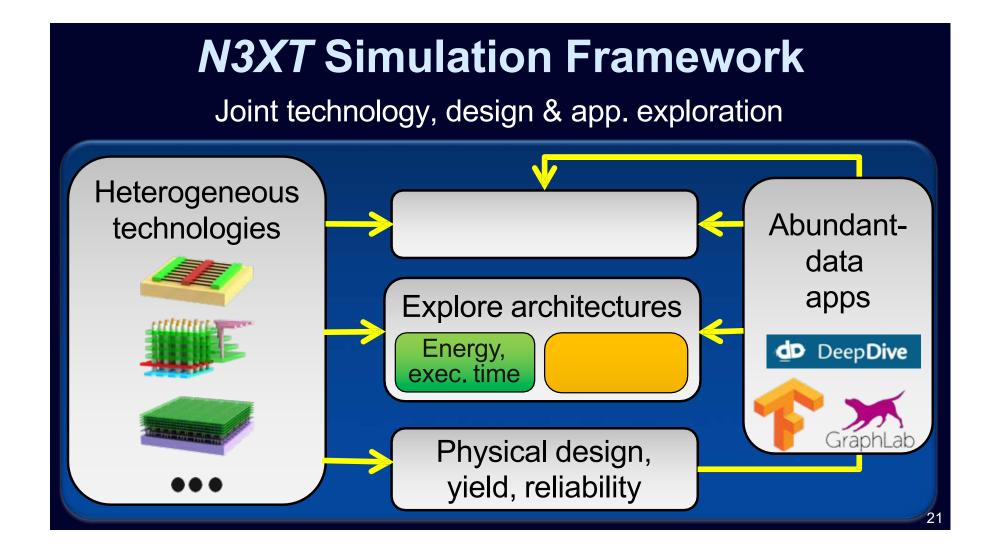
Many chips system

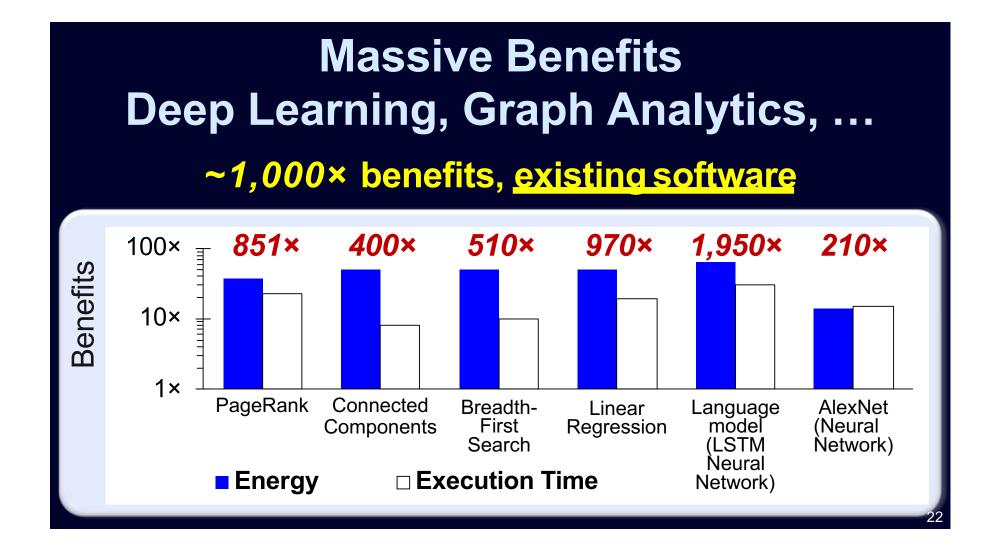
Few chips system

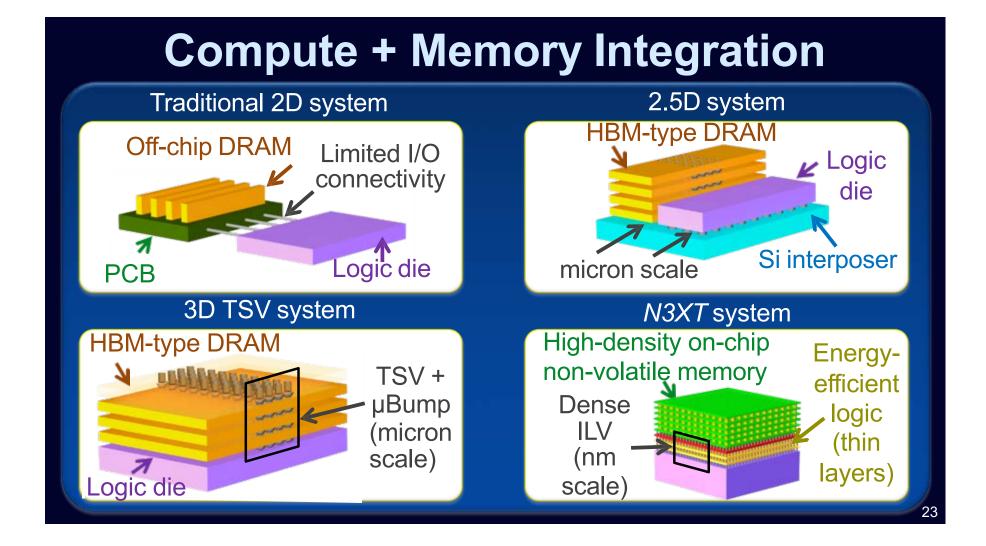
Architecture

Circuit

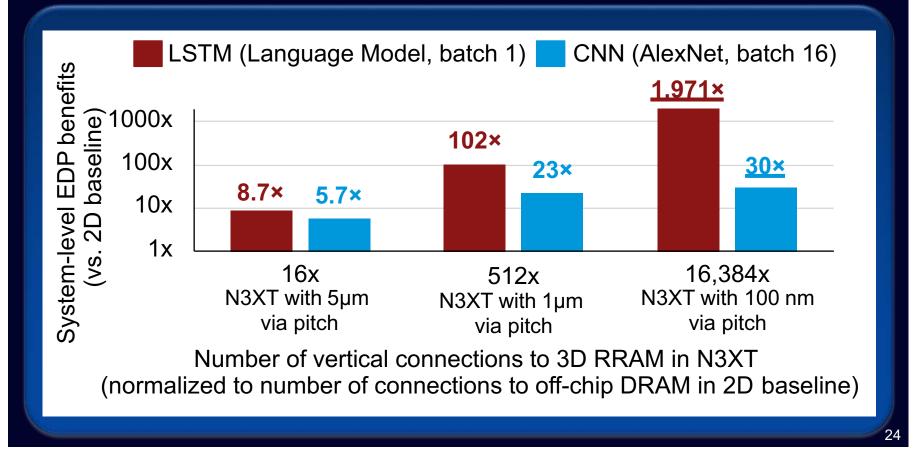
Device



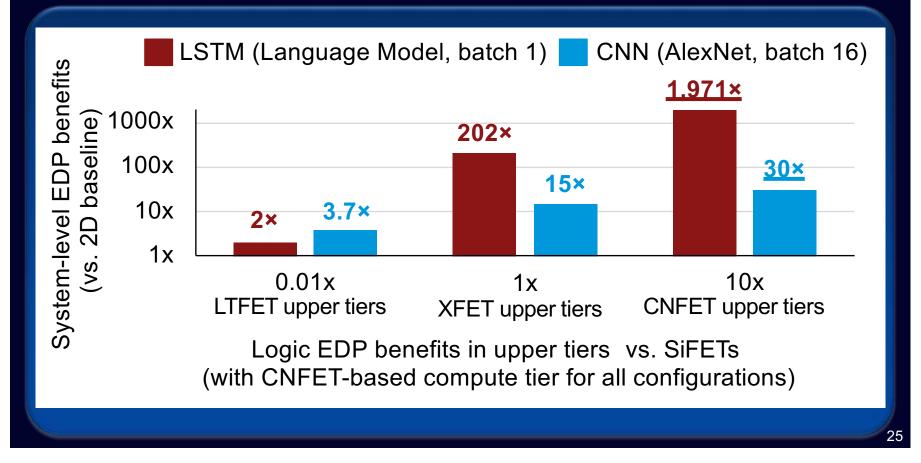


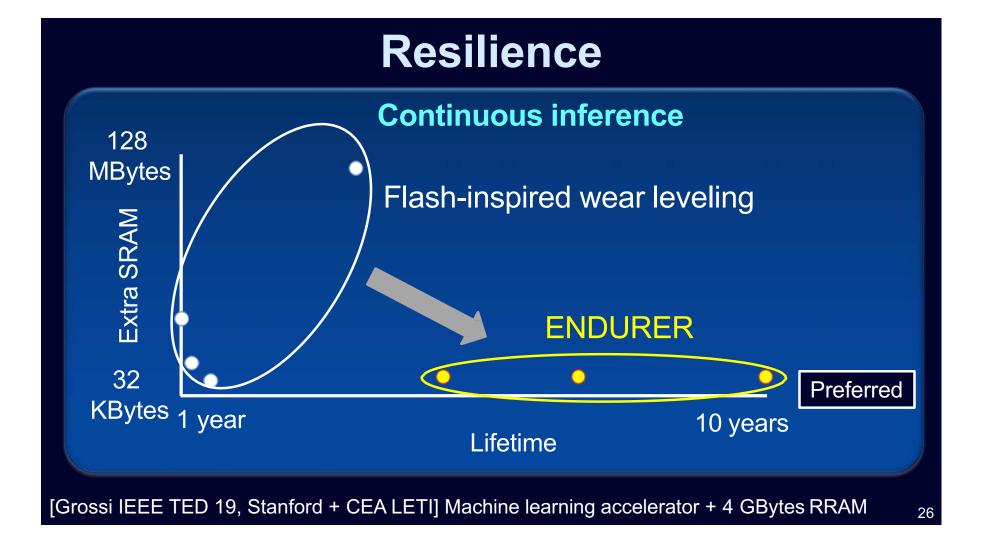


Compute + Memory Integration



Compute + Memory Integration

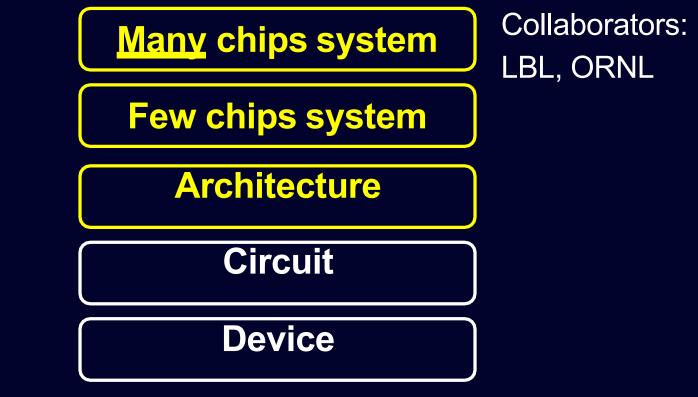


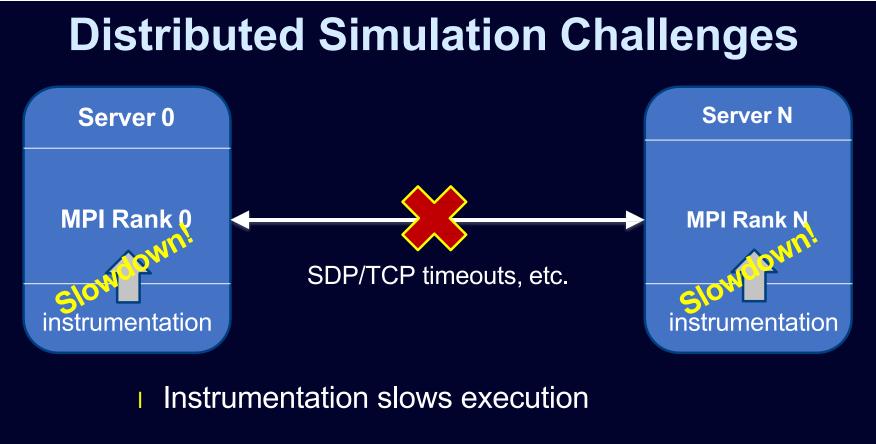


Many More (ModSim) Opportunities

- Software mapping
- New micro-architectures & memory hierarchy
- I Dense compute + thermal

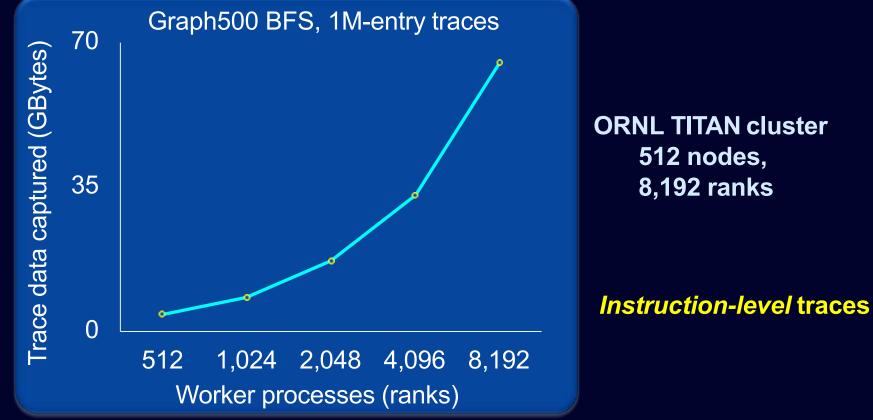
N3XT Cross-Layer ModSim





Remote nodes can't reply before timeout

Ongoing: Decoupled Tracing + ModSim



30

Thanks: Students, Sponsors, Collaborators



Conclusion

NanoSystems today

RRAM, CNFET, dense (monolithic) 3D

In fabs now (from labs)

Many cross-layer opportunities